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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/612,793	07/02/2003	Arup Bhattacharyya	1303.111US1	5437
21186	7590	08/24/2005		EXAMINER
		SCHWEGMAN, LUNDBERG, WOESSNER & KLUTH, P.A.		ERDEM, FAZLI
		P.O. BOX 2938		ART UNIT
		MINNEAPOLIS, MN 55402-0938		PAPER NUMBER
			2826	

DATE MAILED: 08/24/2005

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary	Application No.	Applicant(s)	
	10/612,793	BHATTACHARYYA, ARUP	
	Examiner	Art Unit	
	Fazli Erdem	2826	

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

1) Responsive to communication(s) filed on 16 June 2005.

2a) This action is FINAL. 2b) This action is non-final.

3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

4) Claim(s) 1-100 is/are pending in the application.
4a) Of the above claim(s) 80-100 is/are withdrawn from consideration

5) Claim(s) 1-53 and 72-79 is/are allowed.

6) Claim(s) 54-71 is/are rejected.

7) Claim(s) _____ is/are objected to.

8) Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

9) The specification is objected to by the Examiner.

10) The drawing(s) filed on _____ is/are: a) accepted or b) objected to by the Examiner.

 Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).

 Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).

11) The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
a) All b) Some * c) None of:
1. Certified copies of the priority documents have been received.
2. Certified copies of the priority documents have been received in Application No. _____.
3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

1) Notice of References Cited (PTO-892)
2) Notice of Draftsperson's Patent Drawing Review (PTO-948)
3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date _____
4) Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____
5) Notice of Informal Patent Application (PTO-152)
6) Other: _____

DETAILED ACTION

Allowable Subject Matter

1. Claims 1-53 and 72-79 allowed.
2. The following is a statement of reasons for the indication of allowable subject matter:

Regarding Claims 1 and 6, prior art failed to establish a memory cell having first diffusion region connected to bit line, a second diffusion region which store the memory state of the memory cell, a negative differential resistance diode with an intrinsic region between the anode and cathode to assist with stabilizing the memory stat of the memory cell, connected between the second diffusion region and the reference potential line.

Regarding Claims 7-53, prior art failed to establish a p-channel or n-channel access transistor with a first and second p or n-type diffusion region where the second p or n-type diffusion region store the memory state of the memory cell and a negative differential resistance n/i/p or p/i/n diode having n or p-type anode and cathode with an intrinsic region between the anode and cathode to assist with stabilizing the memory state of the memory cell.

Regarding Claims 72-79, prior art failed to establish a memory device with memory array, word lines, bit lines with access transistor with first and second diffusion regions, a negative differential resistance diode with an intrinsic region between the anode and the cathode where the memory cell is used to store charge in the second diffusion region .

Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

Art Unit: 2826

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

3. Claims 54-71 rejected under 35 U.S.C. 103(a) as being unpatentable over Han (6,611,452) in view of Coe (4,754,310)

Regarding Claims 54-71, Han discloses reference cells fro TCCT based memory cells where a reference cell produces a voltage rise on a bit line that is proportional rise on a another bit line produced by a TCCT based memory cell in an “on” state. The reference cell includes an NDR device, a gate line device disposed adjacent to the NDR device, a first resistive element coupled between the NDR device and the bit line, and a second resistive element coupled between a sink and the bit line. Han fails to disclose the required intrinsic region requirement. However, Coe discloses a high voltage semiconductor device where in Fig. 1, the intrinsic region made up of alternating layers 11 and 12 is situated between anode and cathode 21 and 23.

It would have been obvious to one of having ordinary skill in the art at the time the invention was made to include the required intrinsic region configuration in Han as taught by Coe in order to have a memory cell with higher performance.

Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Fazli Erdem whose telephone number is (571) 272-1914. The examiner can normally be reached on M - F 8:00 - 5:00.



NATHAN J. FLYNN
SUPERVISORY PATENT EXAMINER
TECHNOLOGY CENTER 2800

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (571) 272-1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

FE
August 18, 2005